

## EconoPACK™3 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

### Features

- Electrical features
  - $V_{CES} = 1200\text{ V}$
  - $I_{C\text{nom}} = 200\text{ A} / I_{CRM} = 400\text{ A}$
  - Low  $V_{CE,sat}$
  - Overload operation up to  $175^\circ\text{C}$
  - TRENCHSTOP™ IGBT7
- Mechanical features
  - Integrated NTC temperature sensor
  - High power and thermal cycling capability
  - Solder contact technology
  - $\text{Al}_2\text{O}_3$  substrate with low thermal resistance
  - Copper base plate



Typical appearance

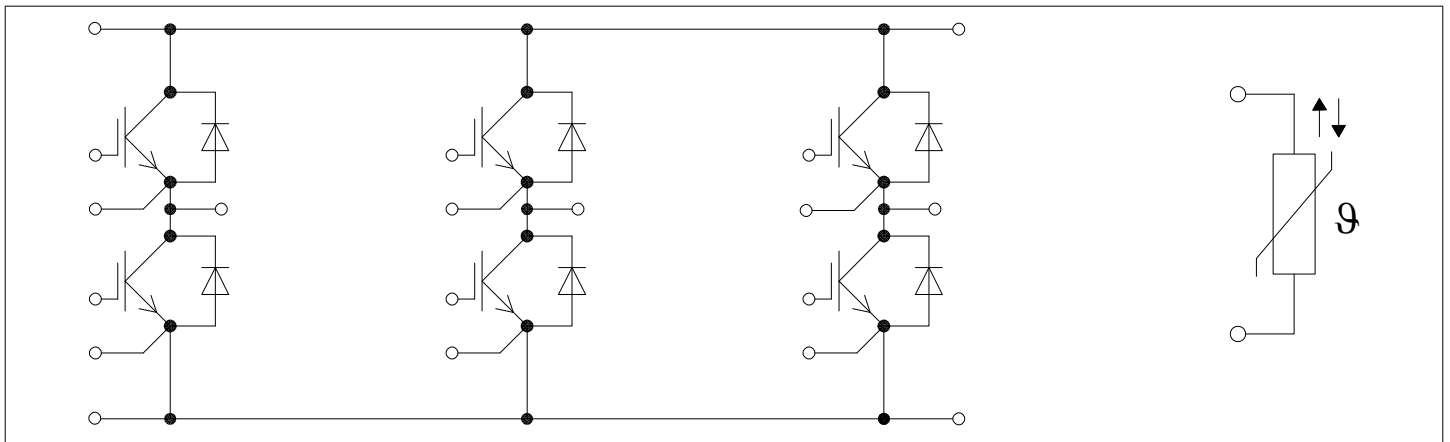
### Potential applications

- Motor drives
- Auxiliary inverters
- Servo drives

### Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

### Description



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## 1 Package

**Table 1 Insulation coordination**

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	$V_{ISOL}$	RMS, $f = 50$ Hz, $t = 1$ min	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	$Al_2O_3$	
Creepage distance	$d_{Creep}$	terminal to heatsink	10.0	mm
Clearance	$d_{Clear}$	terminal to heatsink	7.5	mm
Comparative tracking index	$CTI$		>200	
Relative thermal index (electrical)	$RTI$	housing	140	°C

**Table 2 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{SCE}$			30		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ C$ , per switch		1.5		mΩ
Storage temperature	$T_{stg}$		-40		125	°C
Mounting torque for module mounting	$M$	- Mounting according to valid application note		3	6	Nm
Weight	$G$			300		g

Note: The current under continuous operation is limited to 50 A rms per connector pin.

## 2 IGBT, Inverter

**Table 3 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	$V_{CES}$	$T_{vj} = 25^\circ C$	1200	V
Continuous DC collector current	$I_{CDC}$	$T_{vj\ max} = 175^\circ C$ $T_C = 75^\circ C$	200	A
Repetitive peak collector current	$I_{CRM}$	$t_p$ limited by $T_{vj\ op}$	400	A
Gate-emitter peak voltage	$V_{GES}$		±20	V

**Table 4 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 200\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.55	1.80	V
			$T_{vj} = 125\ ^\circ C$	1.69		
			$T_{vj} = 175\ ^\circ C$	1.77		
Gate threshold voltage	$V_{GETh}$	$I_C = 4.6\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.15	5.80	6.45	V
Gate charge	$Q_G$	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$		3.34		$\mu C$
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\ ^\circ C$		0.75		$\Omega$
Input capacitance	$C_{ies}$	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		40.3		nF
Reverse transfer capacitance	$C_{res}$	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.14		nF
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		0.016	mA
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			100	nA
Turn-on delay time (inductive load)	$t_{don}$	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.172		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.184		
			$T_{vj} = 175\ ^\circ C$	0.192		
Rise time (inductive load)	$t_r$	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.063		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.073		
			$T_{vj} = 175\ ^\circ C$	0.074		
Turn-off delay time (inductive load)	$t_{doff}$	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.352		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.442		
			$T_{vj} = 175\ ^\circ C$	0.486		
Fall time (inductive load)	$t_f$	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.092		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.190		
			$T_{vj} = 175\ ^\circ C$	0.254		
Turn-on energy loss per pulse	$E_{on}$	$I_C = 200\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 3\ \Omega, di/dt = 2300\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	25.5		mJ
			$T_{vj} = 125\ ^\circ C$	30.3		
			$T_{vj} = 175\ ^\circ C$	32.8		
Turn-off energy loss per pulse	$E_{off}$	$I_C = 200\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 3\ \Omega, dv/dt = 3100\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	13.6		mJ
			$T_{vj} = 125\ ^\circ C$	20.6		
			$T_{vj} = 175\ ^\circ C$	26.7		

(table continues...)

**Table 4 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
SC data	$I_{SC}$	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$		640		A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$		600		
Thermal resistance, junction to case	$R_{thJC}$	per IGBT			0.231	K/W	
Thermal resistance, case to heat sink	$R_{thCH}$	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m} \cdot \text{K})$		0.0690		K/W	
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$	

Note:  $T_{vj op} > 150 \text{ }^\circ\text{C}$  is only allowed for operation at overload conditions. For detailed specifications please refer to AN 2018-14.

### 3 Diode, Inverter

**Table 5 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V	
Continuous DC forward current	$I_F$		200	A	
Repetitive peak forward current	$I_{FRM}$	$t_p = 1 \text{ ms}$	400	A	
$I^2t$ - value	$I^2t$	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	5190	$\text{A}^2\text{s}$
			$T_{vj} = 175 \text{ }^\circ\text{C}$	4690	

**Table 6 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	$V_F$	$I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.72	2.10	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.59		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.52		
Peak reverse recovery current	$I_{RM}$	$V_R = 600 \text{ V}, I_F = 200 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 2300 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		92.5		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		134		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		149		

(table continues...)

**Table 6 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	$Q_r$	$V_R = 600\text{ V}, I_F = 200\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 2300\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	13		$\mu\text{C}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	27.3		
			$T_{vj} = 175\text{ }^\circ\text{C}$	36.5		
Reverse recovery energy	$E_{rec}$	$V_R = 600\text{ V}, I_F = 200\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 2300\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	3.65		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	8.94		
			$T_{vj} = 175\text{ }^\circ\text{C}$	11.8		
Thermal resistance, junction to case	$R_{thJC}$	per diode			0.376	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.0680		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$

Note:  $T_{vj\text{ op}} > 150\text{ }^\circ\text{C}$  is only allowed for operation at overload conditions. For detailed specifications please refer to AN 2018-14.

## 4 NTC-Thermistor

**Table 7 Characteristic values**

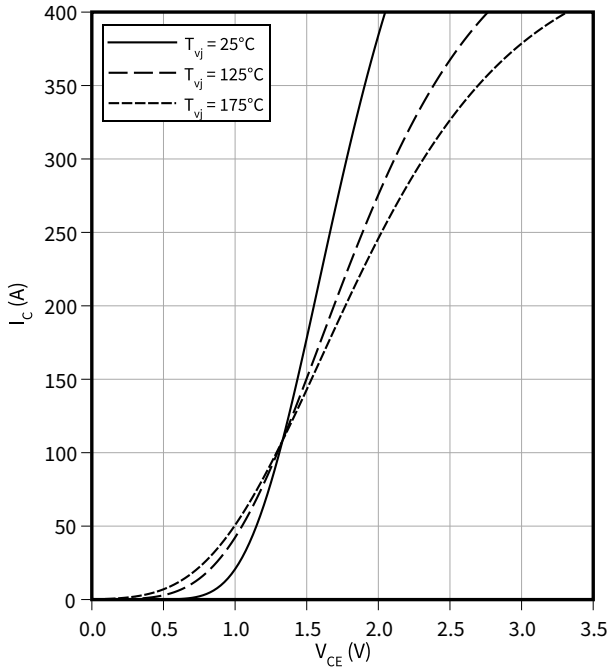
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	$R_{25}$	$T_{NTC} = 25\text{ }^\circ\text{C}$		5		k $\Omega$
Deviation of $R_{100}$	$\Delta R/R$	$T_{NTC} = 100\text{ }^\circ\text{C}, R_{100} = 493\text{ }\Omega$	-5		5	%
Power dissipation	$P_{25}$	$T_{NTC} = 25\text{ }^\circ\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

Note: Specification according to the valid application note.

## 5 Characteristics diagrams

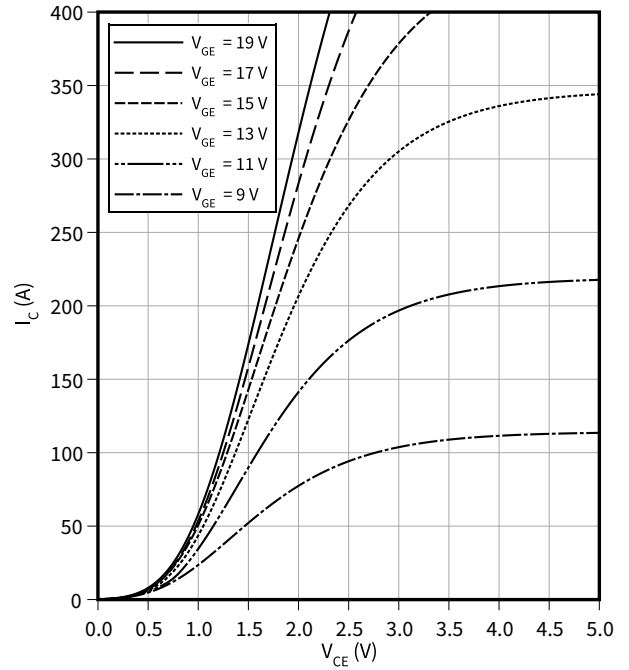
**Output characteristic (typical), IGBT, Inverter**

$I_C = f(V_{CE})$   
 $V_{GE} = 15 \text{ V}$



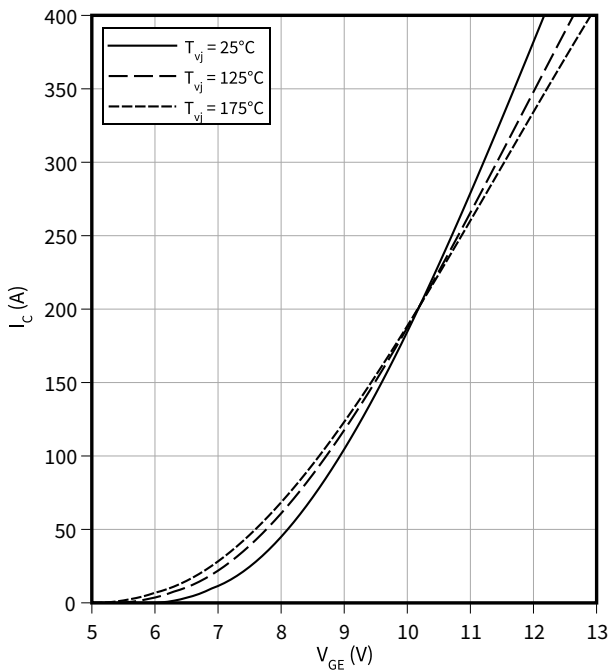
**Output characteristic field (typical), IGBT, Inverter**

$I_C = f(V_{CE})$   
 $T_{vj} = 175 \text{ °C}$



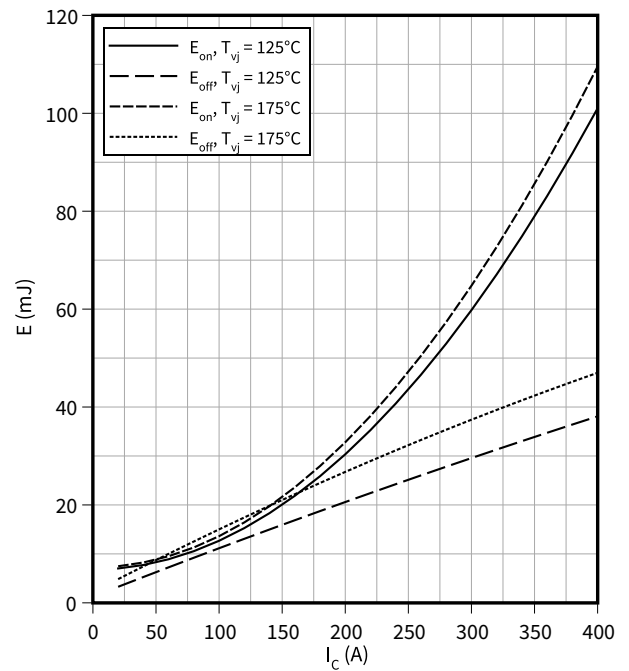
**Transfer characteristic (typical), IGBT, Inverter**

$I_C = f(V_{GE})$   
 $V_{CE} = 20 \text{ V}$



**Switching losses (typical), IGBT, Inverter**

$E = f(I_C)$   
 $R_{Goff} = 3.0 \text{ } \Omega$ ,  $R_{Gon} = 3.0 \text{ } \Omega$ ,  $V_{CE} = 600 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$

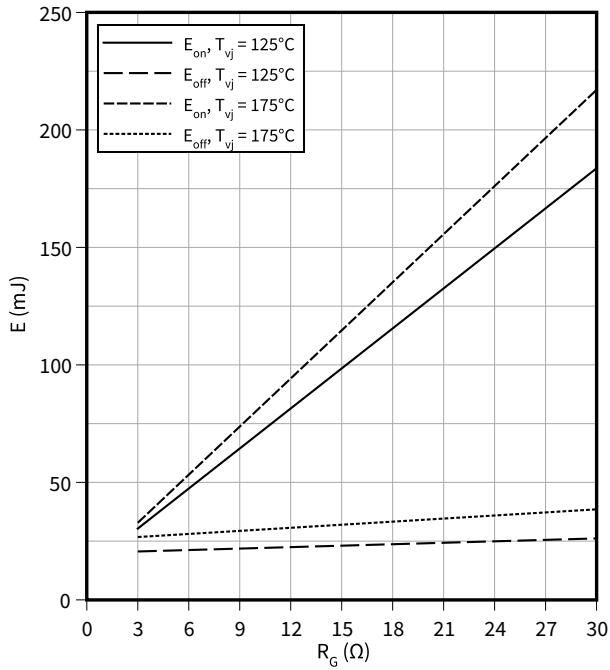


5 Characteristics diagrams

**Switching losses (typical), IGBT, Inverter**

$E = f(R_G)$

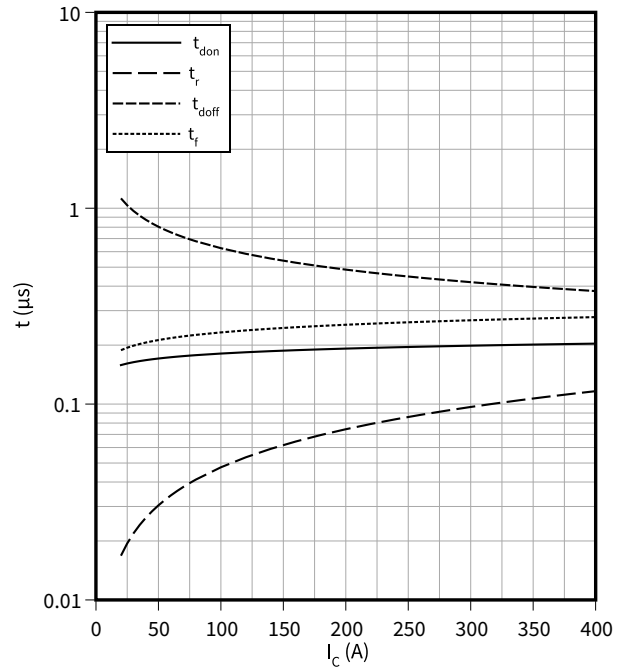
$I_C = 200 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$



**Switching times (typical), IGBT, Inverter**

$t = f(I_C)$

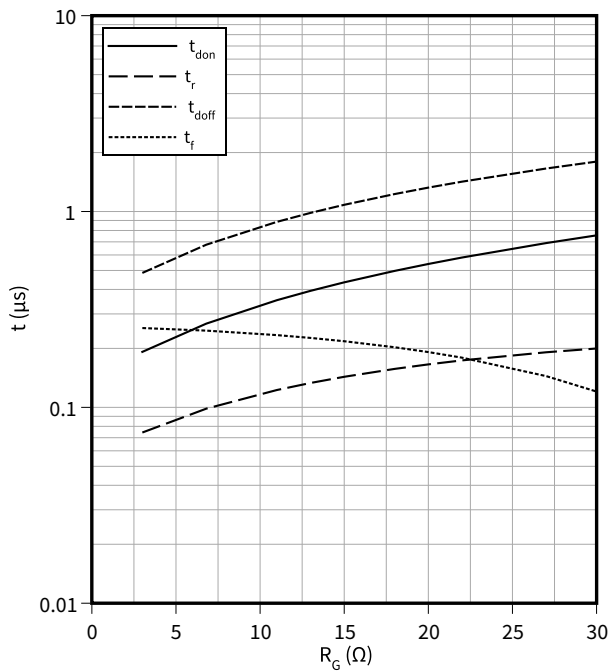
$R_{Goff} = 3.0 \text{ } \Omega, R_{Gon} = 3.0 \text{ } \Omega, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ } ^\circ\text{C}$



**Switching times (typical), IGBT, Inverter**

$t = f(R_G)$

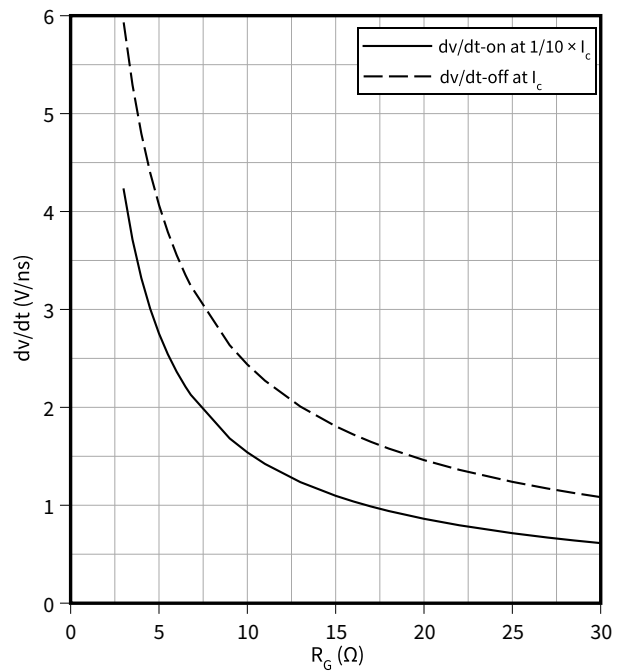
$I_C = 200 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ } ^\circ\text{C}$



**Voltage slope (typical), IGBT, Inverter**

$dv/dt = f(R_G)$

$I_C = 200 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 25 \text{ } ^\circ\text{C}$

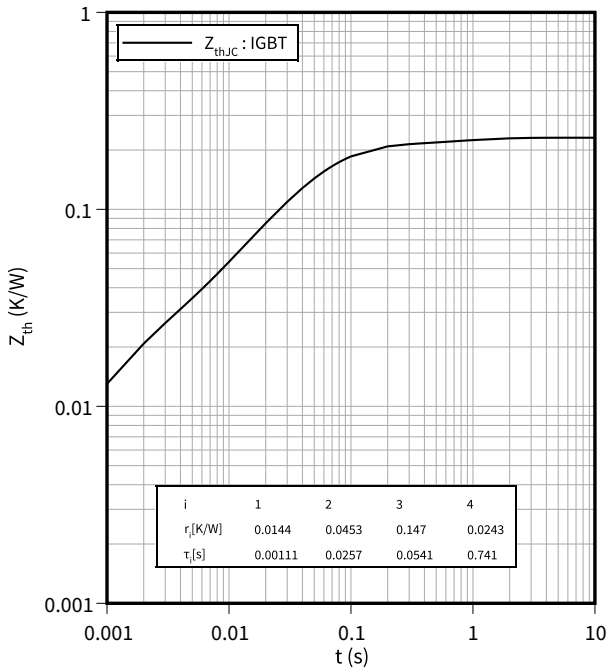




5 Characteristics diagrams

**Transient thermal impedance, IGBT, Inverter**

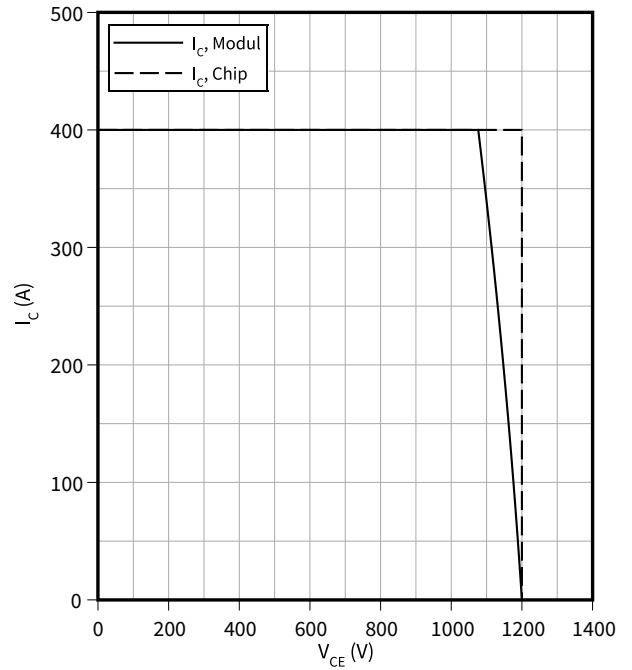
$Z_{th} = f(t)$



**Reverse bias safe operating area (RBSOA), IGBT, Inverter**

$I_C = f(V_{CE})$

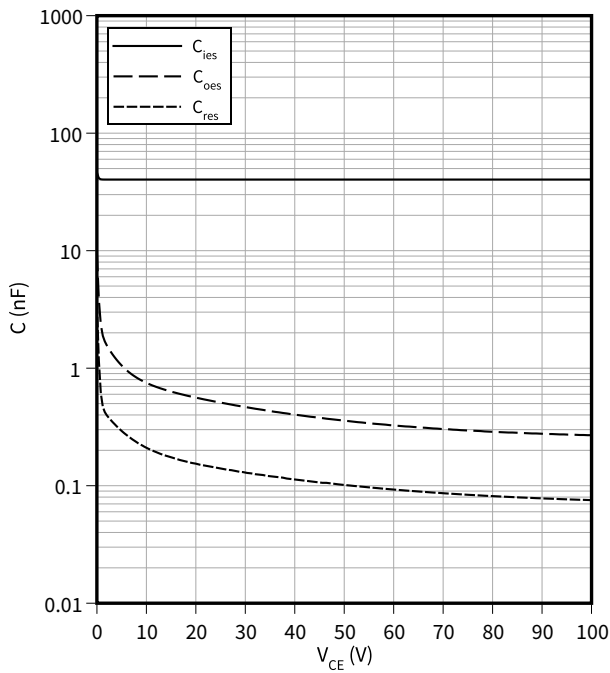
$T_{vj} = 175\text{ °C}$ ,  $R_{Goff} = 3.0\ \Omega$ ,  $V_{GE} = \pm 15\text{ V}$



**Capacity characteristic (typical), IGBT, Inverter**

$C = f(V_{CE})$

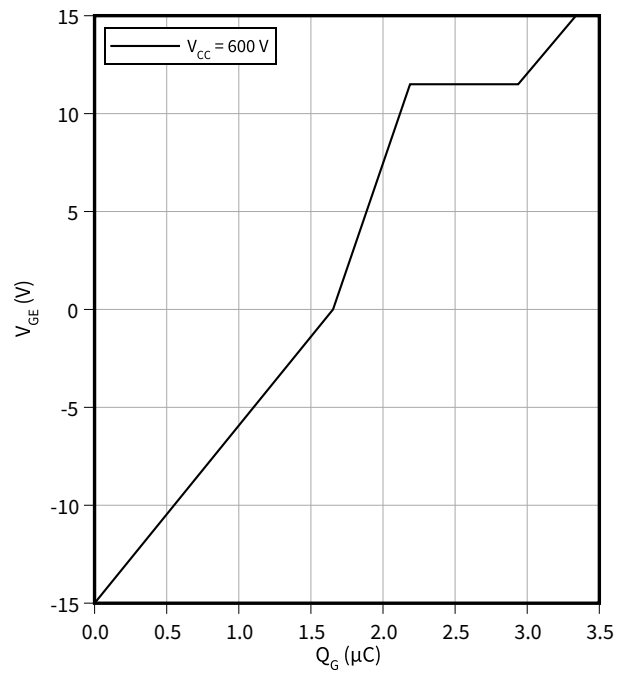
$f = 100\text{ kHz}$ ,  $V_{GE} = 0\text{ V}$ ,  $T_{vj} = 25\text{ °C}$



**Gate charge characteristic (typical), IGBT, Inverter**

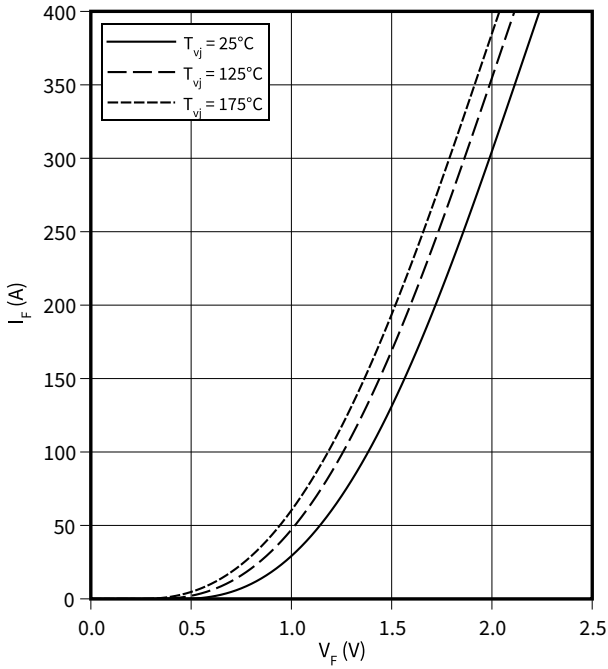
$V_{GE} = f(Q_G)$

$I_C = 200\text{ A}$ ,  $T_{vj} = 25\text{ °C}$



**Forward characteristic (typical), Diode, Inverter**

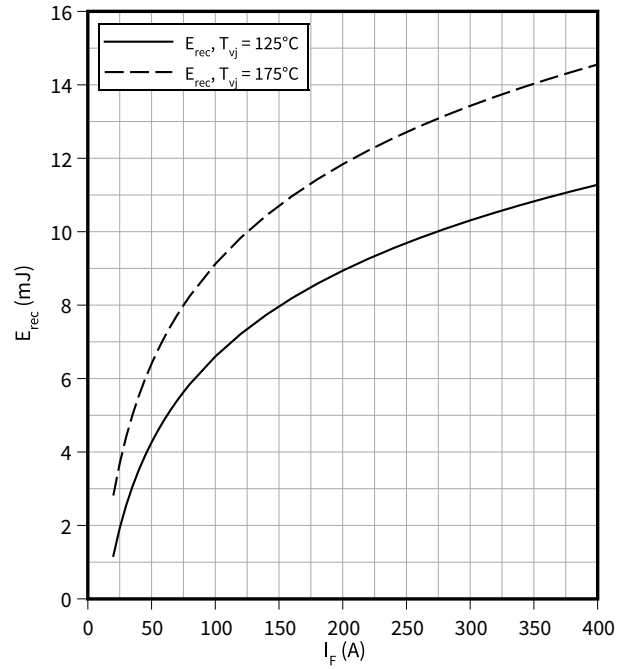
$I_F = f(V_F)$



**Switching losses (typical), Diode, Inverter**

$E_{rec} = f(I_F)$

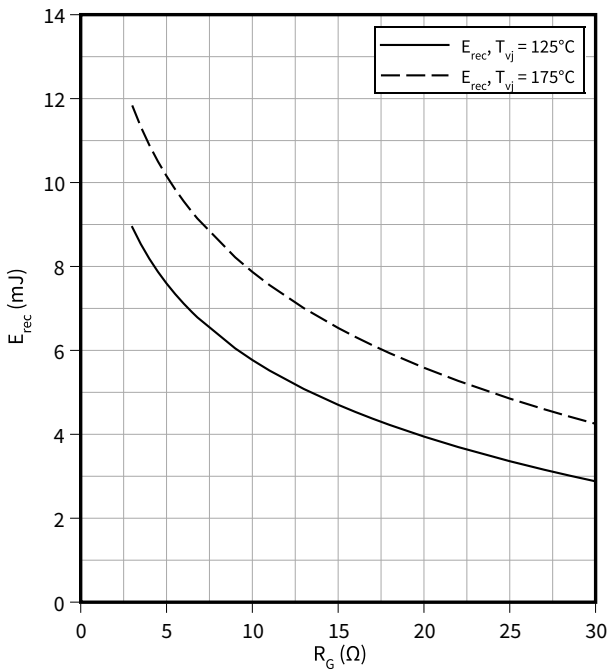
$R_{Gon} = 3.0 \Omega, V_R = 600 \text{ V}$



**Switching losses (typical), Diode, Inverter**

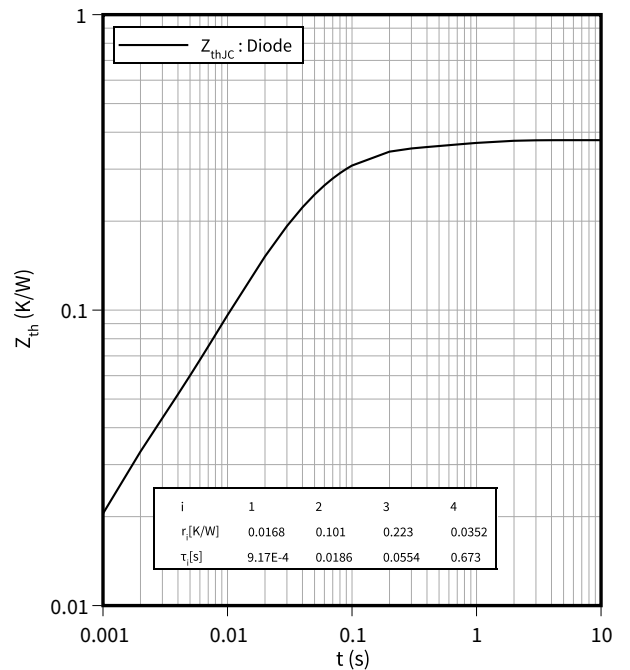
$E_{rec} = f(R_G)$

$I_F = 200 \text{ A}, V_R = 600 \text{ V}$



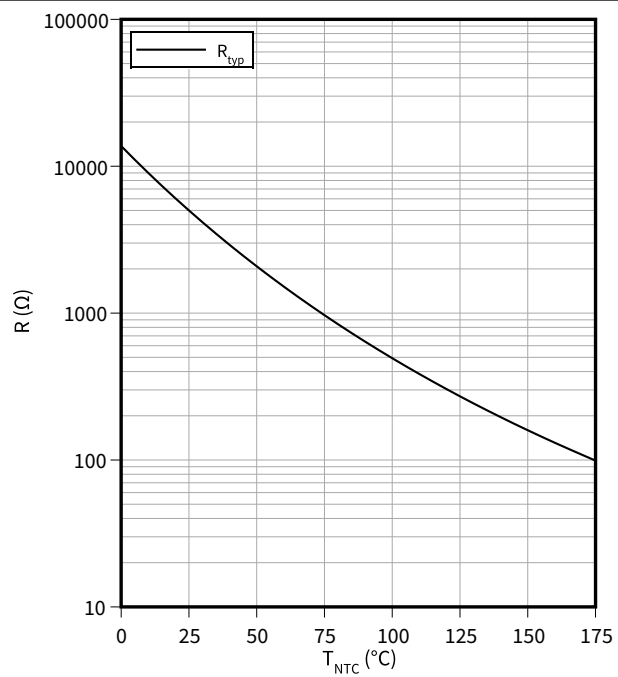
**Transient thermal impedance, Diode, Inverter**

$Z_{th} = f(t)$



**Temperature characteristic (typical), NTC-Thermistor**

$R = f(T_{NTC})$



## 6 Circuit diagram

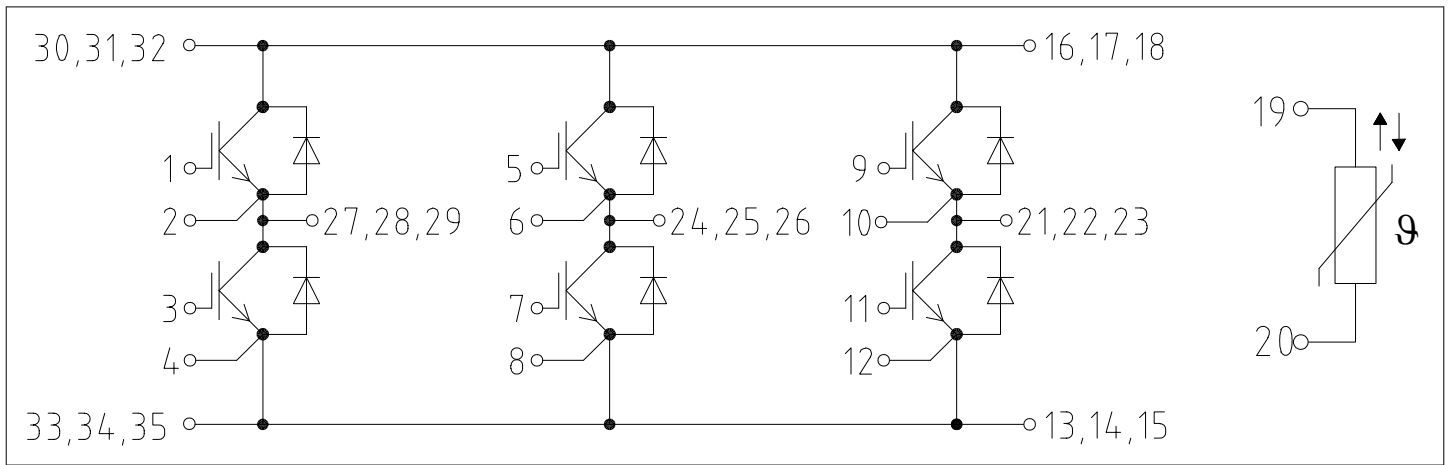


Figure 1

## 7 Package outlines

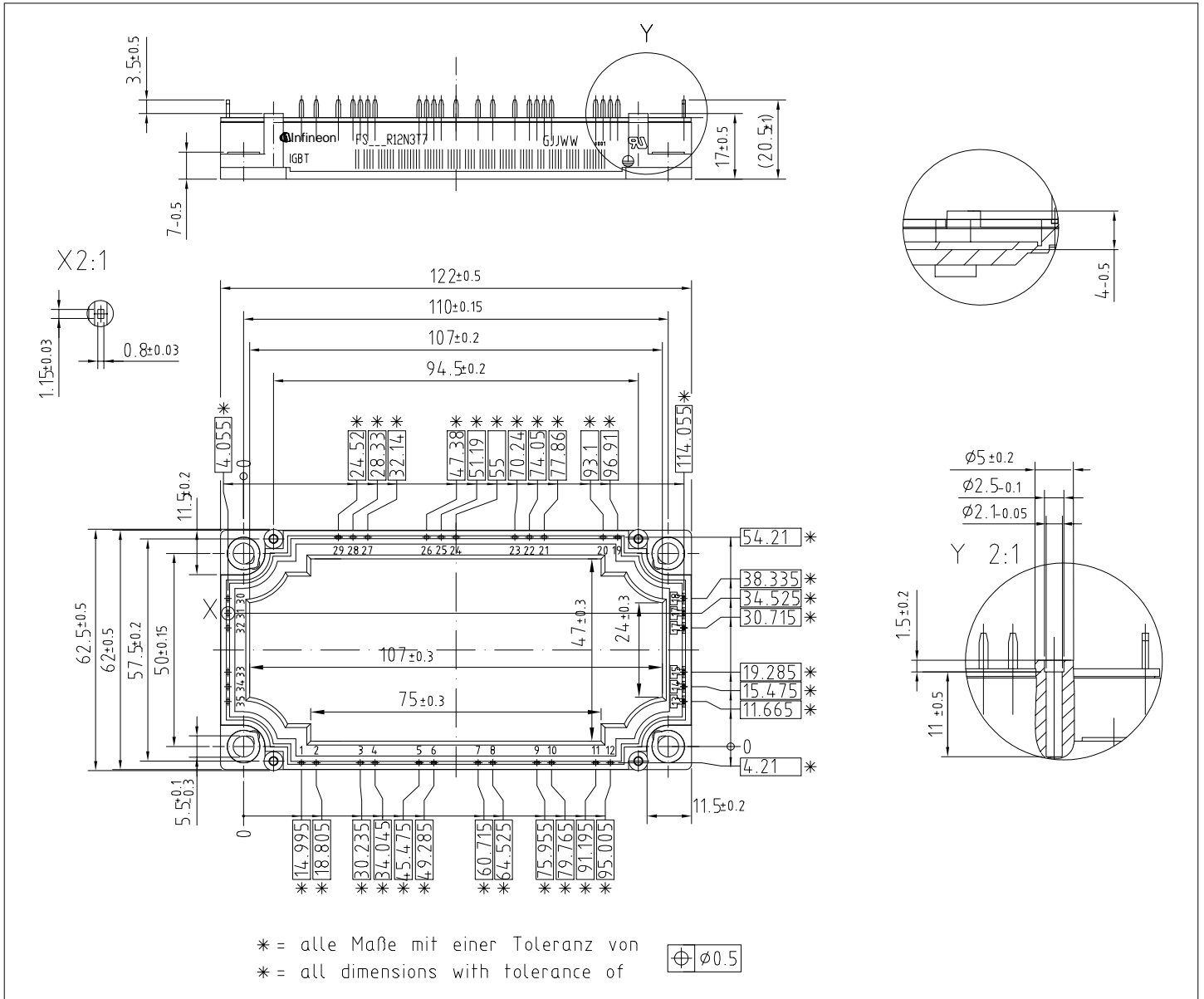

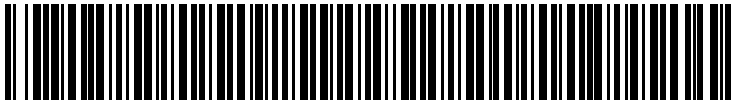


Figure 2

## 8 Module label code

Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	Content	Digit	Example
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example			
	71549142846550549911530		71549142846550549911530

**Figure 3**

## Revision history

Document revision	Date of release	Description of changes
V1.0	2019-09-11	Target datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2022-03-02	Final datasheet

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**Document reference**

**IFX-AAY224-002**

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